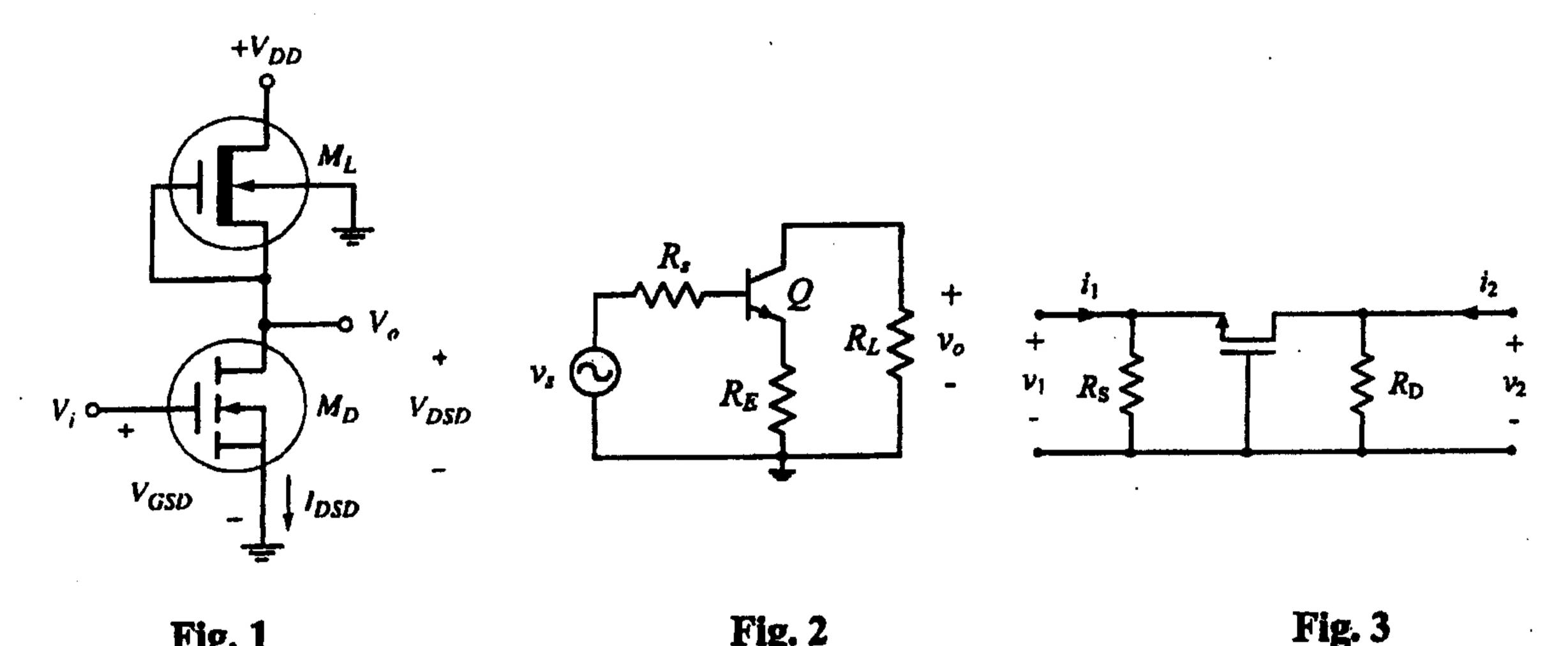
系所:微電子工程研究所,量机条7亿、7、7位4、量通价的订超 科目:電子學

本試題是否可以使用計算機: ☑可使用 □不可使用 (請命題老師勾選) 考試日期:0301,節次:1

- 1. A doped silicon sample is 3 mm long and has a rectangular cross section of  $50\times100~\mu\text{m}^2$ . The donor concentration is  $5\times10^{14}~\text{cm}^{-3}$ . A steady current of 1  $\mu$ A exists in the bar. Determine the conductivity and voltage across the bar. (if the related parameters are:  $\mu_n=1500~\text{cm}^2/\text{V·s}$ ,  $\mu_p=475~\text{cm}^2/\text{V·s}$ , and  $n_i=1.5\times10^{10}~\text{cm}^{-3}$ ) (12%)
- 2. An NMOS inverter with a depletion-type load is shown in Fig. 1. The related parameters of this circuit are  $V_{\rm DD}=5$  V,  $K_{\rm D}=90~\mu \text{A/V}^2$ ,  $V_{\rm TD}=1$  V,  $K_{\rm L}=30~\mu \text{A/V}^2$ , and  $V_{\rm TL}=-2$  V. Determine the noise margins (NM<sub>L</sub> and NM<sub>H</sub>) of this circuit. (20%)



- Fig. 1 Fig. 2 Fig. 3

  3. Calculate gain-bandwidth product (GBP) and cutoff frequency of the amplifier shown
- in Fig. 2 for the case of  $R_E=0\,k\Omega$  and  $R_E=0.1\,k\Omega$ , respectively. Assume  $R_S=0.5\,k\Omega$ ,  $R_L=r_\pi=1\,k\Omega$ ,  $C_\pi=50\,pF$ ,  $C_\mu=1\,pF$ , and  $\beta=100$  · (16%)
- 4. (a) Find the midband gain in dB and bandwidth in Hz for the amplifier described by  $A(s) = \frac{2.5 \times 10^7 (s + 2 \times 10^5)}{(s + 10^5)(s + 5 \times 10^5)}$ . What type of amplifier is this? (6%)
  - (b) Write the g-parameter description of the common-gate amplifier shown in Fig. 3. What are the values of  $g_{12}$  and  $g_{21}$  if  $R_S=20~\mathrm{k}\Omega$ ,  $R_D=100~\mathrm{k}\Omega$ ,  $g_m=400~\mathrm{\mu}\mathrm{S}$ , and  $r_o=400~\mathrm{k}\Omega$ . (12%)

(背面仍有題目,請繼續作答)

編號: 214,213,227 國立成功大學九十七學年度可

圖立成功大學九十七學年度碩士班招生考試試題

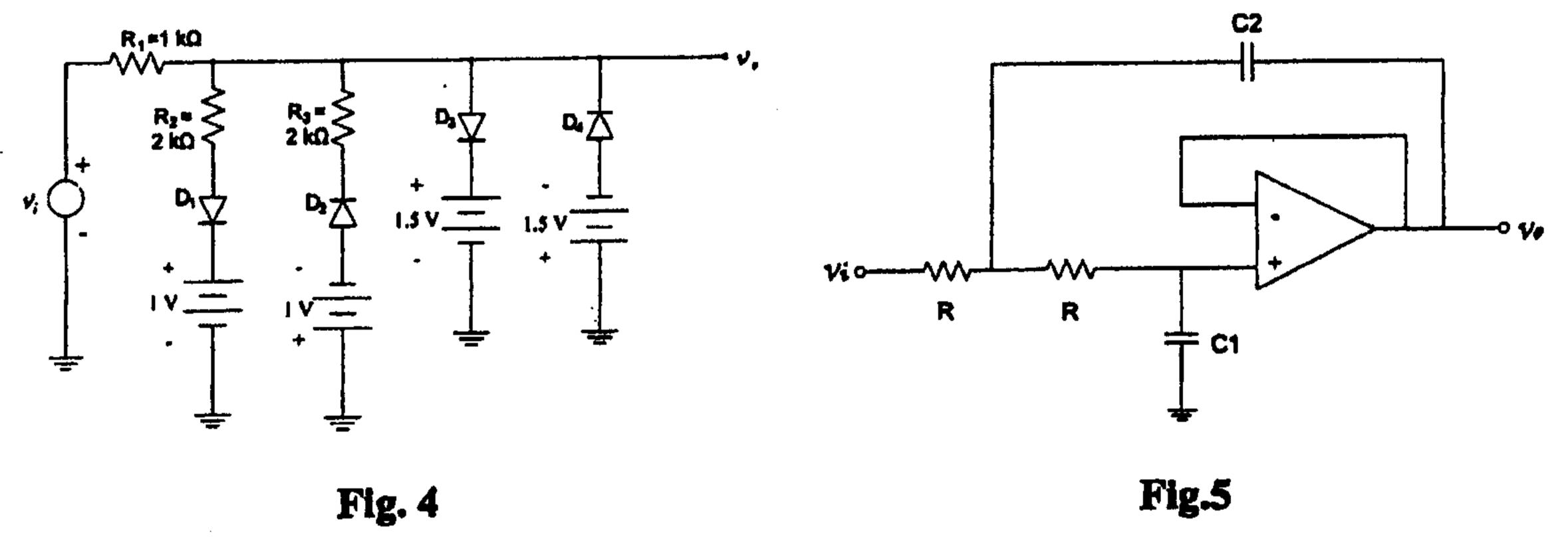
共 2 頁·第2頁

系所:微電子工程研究所,電机条甲2.7.戊血,量血价品.7.40 科目:電子學

本試題是否可以使用計算機: ②可使用 · □不可使用 (請命題老師勾選)

考試日期:0301·節次:

- 5. An amplifier with a single-pole low-pass transfer function with a DC gain of 400 and a pole at 1 kHz also has  $R_i=1$  k $\Omega$  and  $R_o=750$   $\Omega$ . We want to use this amplifier in a negative-feedback connection to produce a close-loop amplifier with a gain of 10. We want to achieve the smallest input resistance and largest output resistance possible
  - (a) What type of feedback connection should we use? (4%)
  - (b) What value of feedback factor, β, is required? (4%)
  - (c) What are the resulting values of the input resistance and output resistance for the feedback amplifier? (4%)
  - (d) What is the resulting closed-loop bandwidth? (4%)
- 6. Consider the circuit shown in Fig. 4. Assume that the diodes are ideal. Plot the transfer characteristic of this circuit,  $v_o/v_i$ , for  $-2V \le v_i \le 2V$ . (6%)



- 7. Consider the OP-Amp circuit shown in Fig. 5. Assume that the OP-Amp is ideal.
  - (a) Find the transfer function,  $T(s) = \frac{v_0(s)}{v_i(s)}$ . (6%)
  - (b) Sketch the Bode plots of the magnitude and phase of the transfer function for  $R=100 \text{ k}\Omega$ ,  $C_1=56.3 \text{ pF}$ ,  $C_2=113 \text{ pF}$ . (6%)